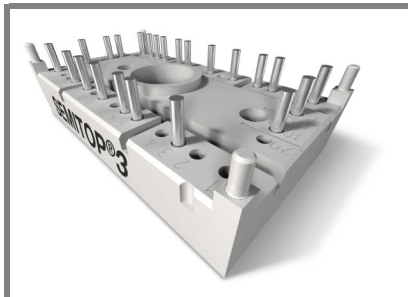


SK25GD063



SEMITOP® 3

IGBT Module

SK25GD063

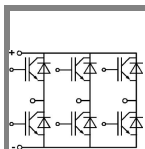
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchthrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63532

Typical Applications*

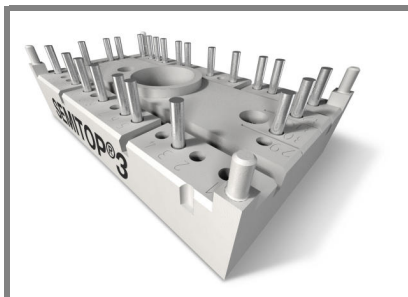
- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



GD

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V _{CES}	T _j = 25 °C	600	V
I _C	T _j = 125 °C	T _s = 25 °C	30 A
		T _s = 80 °C	21 A
I _{CRM}	I _{CRM} = 2 × I _{Cnom}	60	A
V _{GES}		± 20	V
t _{psc}	V _{CC} = 300 V; V _{GE} ≤ 20 V; T _j = 125 °C V _{CES} < 600 V	10	μs
Inverse Diode			
I _F	T _j = 150 °C	T _s = 25 °C	36 A
		T _s = 80 °C	24 A
I _{FRM}	I _{FRM} = 2 × I _{Fnom}		A
I _{FSM}	t _p = 10 ms; half sine wave T _j = 150 °C	200	A
Module			
I _{t(RMS)}			A
T _{vj}		-40 ... +150	°C
T _{stg}		-40 ... +125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics		T _s = 25 °C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0,7 mA	4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C		0,1	mA
		T _j = 125 °C			mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 30 V	T _j = 25 °C		120	nA
		T _j = 125 °C			nA
V _{CE0}		T _j = 25 °C	1		V
		T _j = 125 °C	1,1		V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C	37		mΩ
		T _j = 125 °C	30		mΩ
V _{CE(sat)}	I _{Cnom} = 30 A, V _{GE} = 15 V	T _j = 25 °C _{chiplev.}	2,1	2,5	V
		T _j = 125 °C _{chiplev.}	2	2,3	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz		1,3		nF
C _{oes}					nF
C _{res}		0,1		nF	
Q _G	V _{GE} = 0 ... 20 V		125		nC
t _{d(on)}	R _{Gon} = 33 Ω	V _{CC} = 300V I _C = 25A	40		ns
t _r			50		ns
E _{on}			1,3		mJ
t _{d(off)}	R _{Goff} = 33 Ω	T _j = 125 °C V _{GE} = ±15V	200		ns
t _f			25		ns
E _{off}			0,9		mJ
R _{th(j-s)}	per IGBT			1,4	K/W



SEMISTOP® 3

IGBT Module

SK25GD063

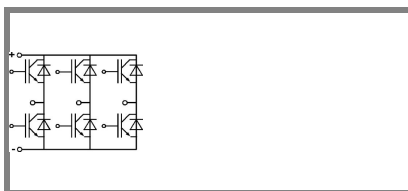
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- N channel, homogeneous Silicon structure (NPT-Non punchthrough IGBT)
- High short circuit capability
- Low tail current with low temperature dependence
- UL recognized, file no. E63532

Typical Applications*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



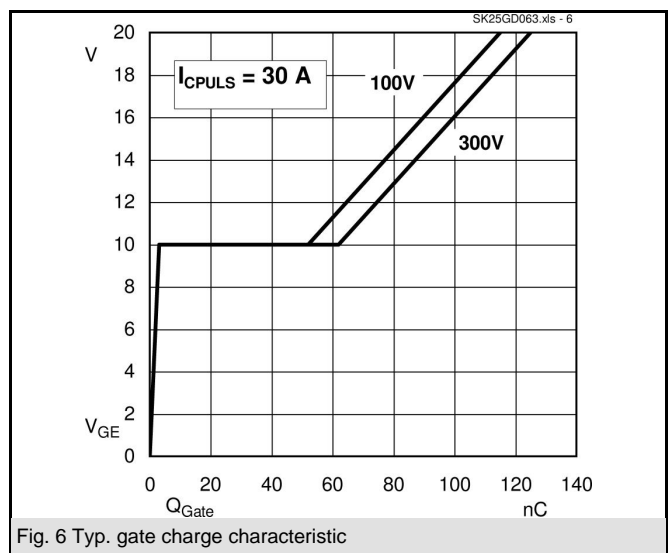
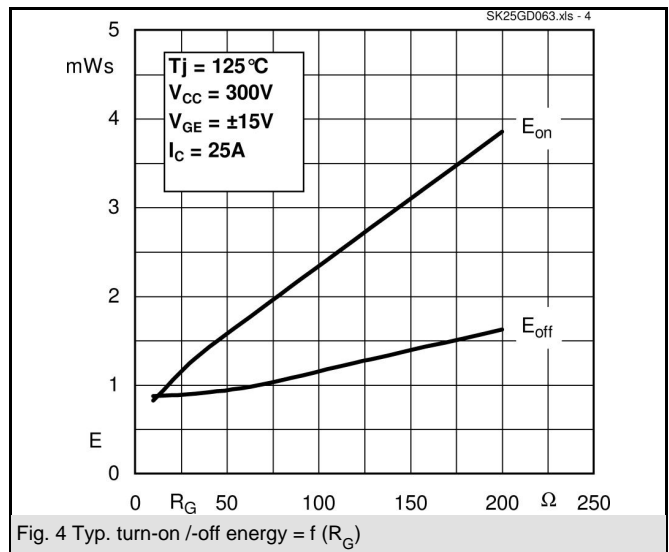
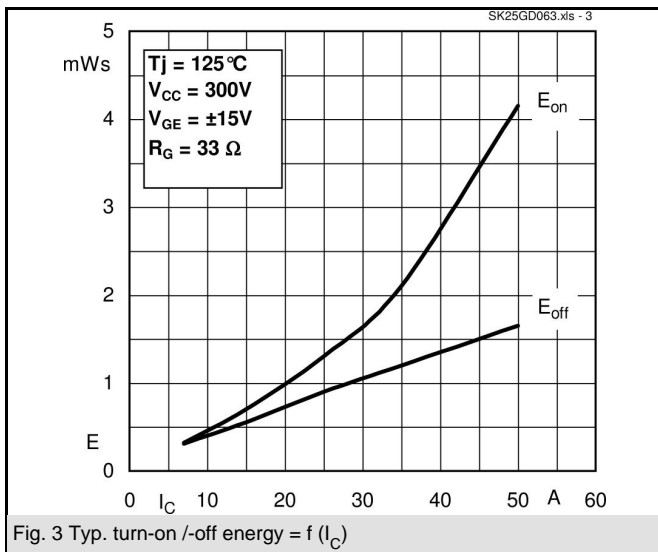
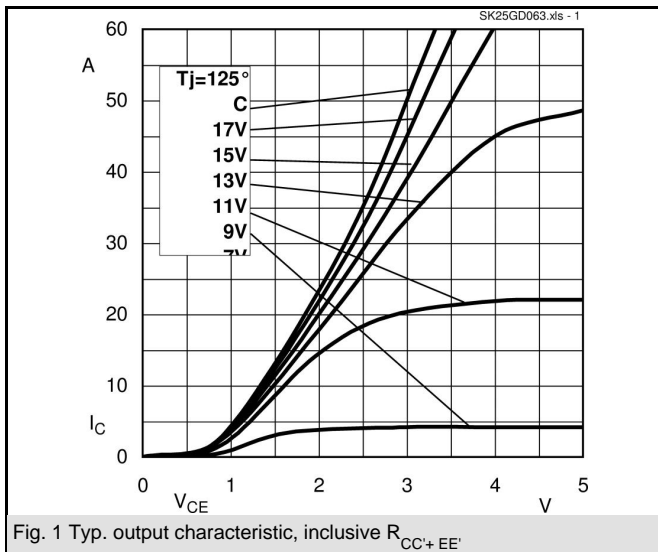
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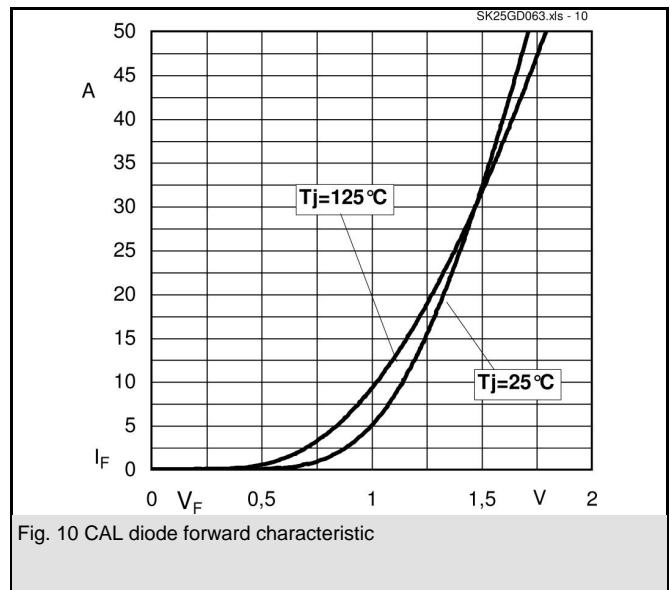
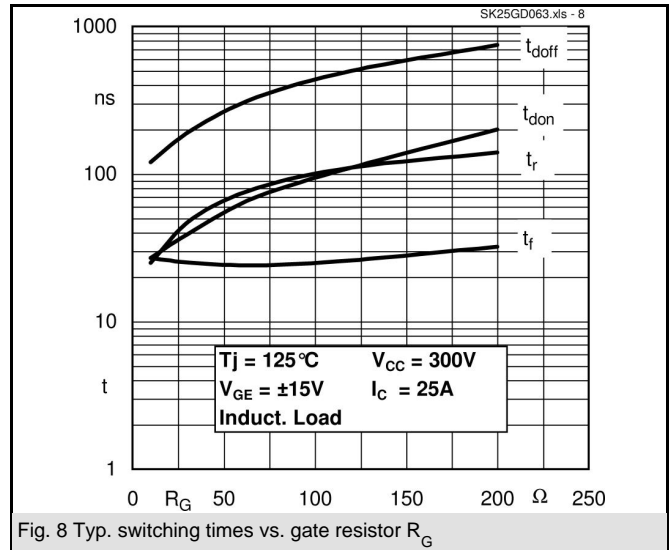
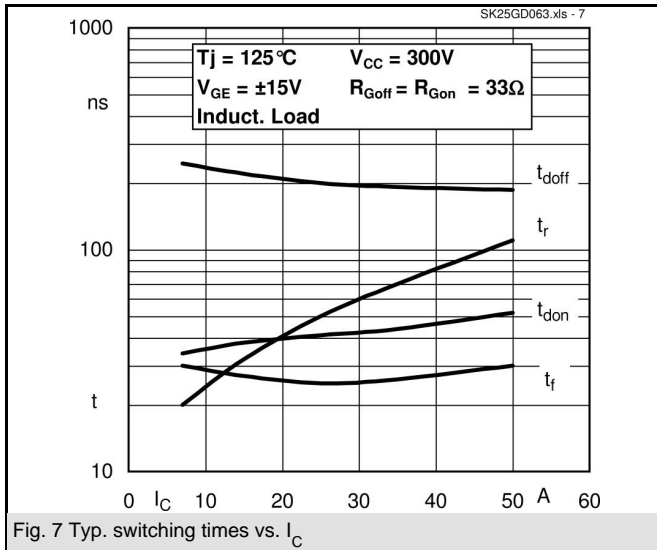
Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 25 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,45	1,7	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,4	1,75	V
V_{F0}			0,85	0,9	V
r_F			22	32	mΩ
I_{RRM}	$I_F = 25 \text{ A}$		16		A
Q_{rr}	$di/dt = -500 \text{ A}/\mu\text{s}$		2		μC
E_{rr}	$V_{CC} = 300\text{V}$		0,25		mJ
$R_{th(j-s)D}$	per diode			1,7	K/W
M_s	to heat sink M1	2,25		2,5	Nm
w			30		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

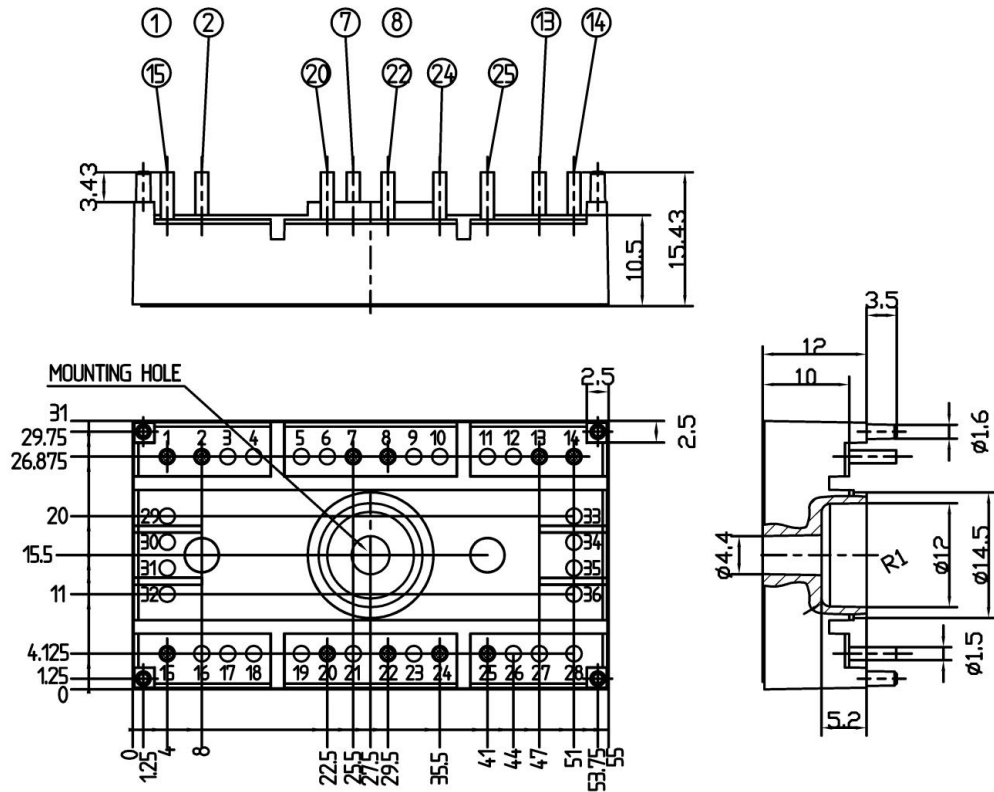




SK25GD063

UL recognized file

no. E 63 532



Case T12 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)

